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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10/789,042
	Filing Date	Even Date Herewith
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2815
	Examiner Name	Unknown R. Wilson
Sheet 1 of 7		Attorney Docket No: 1303.050US2

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
ce	US20020089023	07/11/2002	Yu, Zhiyi , et al.	257	411	01/05/2001
	US20020001971	01/03/2002	Cho, Hag-ju	438	765	06/27/2001
	US20020155688	10/24/2002	Ahn, Kie Y., et al.	438	592	04/20/2001
	US20020155689	10/24/2002	Ahn, Kie Y., et al.	29	76	02/11/2002
	US20020192974	12/19/2002	Ahn, Kie Y., et al.	438	722	06/13/2001
	US20020025628	02/28/2002	Derderian, Garo J., et al.	438	253	06/14/2001
	US20020164420	11/07/2002	Derderian, Garo , et al.	248.1	427	02/25/2002
	US20030017717	01/23/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US20030045082	03/06/2003	Eldridge, Jerome , et al.	438	593	02/20/2002
	US20030207032	11/06/2003	Ahn, Kie Y., et al.	427	255.34	05/02/2002
	US20030207593	11/06/2003	Derderian, Garo J.	438	778	05/02/2002
	US-4,215,156	07/29/1980	Dalal, Hormazdyar M., et al.	427	84	08/26/1977
	US-4,333,808	06/08/1982	Bhattacharyya, Arup , et al.	204	192 D	02/13/1981
	US-4,394,673	07/19/1983	Thompson, Richard D., et al.	357	15	09/29/1980
	US-4,399,424	04/16/1983	Rigby, Leslie J.	338	34	10/05/1981
	US-4,413,022	11/01/1983	Suntola, Tuomo S., et al.	427	255.2	06/21/1979
	US-4,647,947	03/03/1987	Takeoka, Yoshikatsu , et al.	346	135.1	09/13/1985
	US-4,920,071	04/24/1990	Thomas, Michael	437	188	08/18/1987
	US-5,055,319	10/08/1991	Bunshah, Rointan F., et al.	427	38	04/02/1990
	US-5,080,928	01/14/1992	Klinedinst, Keith A., et al.	427	70	10/05/1990
	US-5,198,029	03/30/1993	Dutta, Arunava , et al.	118	303	02/19/1992
	US-5,595,606	01/21/1997	Fujikawa, Yuichiro , et al.	118	725	04/18/1996
	US-5,698,022	12/16/1997	Glassman, Timothy E., et al.			08/14/1996
	US-5,795,808	08/18/1998	Park, Bo	438	301	11/12/1996
	US-5,801,105	09/01/1998	Yano, Yoshihiko , et al.	438	785	06/14/1996
	US-5,810,923	09/22/1998	Yano, Yoshihiko , et al.	117	84	05/10/1996
ce	US-5,822,256	10/13/1998	Bauer, Mark , et al.	365	200	03/05/1997

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DATE CONSIDERED

2/21/06

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Group Art Unit	Unknown <u>2815</u>
Examiner Name	Unknown <u>A. W. Iron</u>

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Attorney Docket No: 1303.050US2

<u>One</u>	US-5,828,080	10/27/1998	Yano, Yoshihiko , et al.	257	43	04/17/1995
	US-5,840,897	11/24/1998	Kirlin, Peter , et al.	546	2	06/07/1995
	US-5,916,365	06/29/1999	Sherman, Arthur	117	92	08/16/1996
	US-5,972,847	10/26/1999	Feenstra, Roeland , et al.	505	473	01/28/1998
	US-6,013,553	01/11/2000	Wallace, Robert , et al.	438	287	07/15/1998
	US-6,020,024	02/01/2000	Maiti, Bikas , et al.	427	248.1	08/04/1997
	US-6,027,961	02/22/2000	Maiti, Bikas , et al.	438	199	06/30/1998
	US-6,057,271	05/02/2000	Kenjiro, Higaki , et al.	505	475	06/07/1995
	US-6,093,944	07/25/2003	VanDover, Robert B.	257	310	06/04/1998
	US-6,110,529	08/29/2000	Gardiner, R. A., et al.	427	250	06/07/1995
	US-6,171,900	01/09/2001	Sun, Shi-Chung	438	240	04/15/1999
	US-6,203,613	03/20/2001	Gates, Stephen M., et al.	117	104	10/19/1999
	US-6,207,589	03/27/2001	Ma, Yanjun , et al.	438	785	02/29/2000
	US-6,211,035	04/03/2001	Moise, Theodore , et al.	438	396	09/09/1999
	US-6,225,168	05/01/2001	Gardner, Mark , et al.	438	287	06/04/1998
	US-6,297,539	10/02/2001	Ma, Yanjun , et al.	257	410	07/06/2000
	US-6,303,481	10/16/2001	Park, Dong	438	591	12/29/2000
	US-6,368,941	04/09/2002	Chen, Tai-Ju , et al.	438	424	11/08/2000
	US-6,380,579	04/30/2002	Nam, Sang-don , et al.	257	306	04/11/2000
	US-6,387,712	05/14/2002	Yano, Yoshihiko , et al.	438	3	12/03/1999
	US-6,391,769	05/21/2002	Lee, Jong-myeong , et al.	438	643	03/14/2000
	US-6,420,230	07/16/2002	Derderian, Garo , et al.	438	255	08/31/2000
	US-6,432,779	08/13/2002	Hobbs, Christopher , et al.	438	287	01/30/2001
	US-6,436,203	08/20/2002	Kaizuka, Takeshi , et al.	148	512	04/18/2000
	US-6,445,023	09/03/2002	Vaartstra, Brian , et al.	257	295	03/16/1999
	US-6,448,192	09/10/2002	Kaushik, Vidya S.	438	785	04/16/2001
	US-6,451,695	09/17/2002	Sneh, Ofer	438	685	12/22/2000
	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
<u>One</u>	US-6,461,436	10/08/2002	Campbell, Philip H., et al.	118	715	10/15/2001

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	Group Art Unit	Unknown 2815
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One	US-6,465,334	10/15/2002	Buynoski, Matthew S., et al.	438	591	10/05/2000
1	US-6,482,740	11/19/2002	Soininen, Pekka J., et al.	438	686	05/15/2001
1	US-6,521,911	02/18/2003	Parsons, Gregory N., et al.	257	52	07/19/2001
One	US-6,627,260	09/30/2003	Derderian, Garo J., et al.	427	301	09/30/2002

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
One	EP-1096042	05/02/2001	Ramdani, J., et al.	C30B	25/02	
	EP-1124262	08/16/2001	Ma, Y., et al.	H01L	29/51	
1	JP-11-335849	12/07/1999	Horie, K., et al.	C23 C	16/44	
	JP-2001-332546	11/30/2001		H01L	21/316	
	WO-01/97257	12/20/2001	Madhukar, S., et al.	H01L	—	
One	WO-02/43115	05/30/2002	Pomarede, C. F., et al.	H01L	—	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
One		AARIK, JAAN, et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , 220(1-2), (2000), 105-113 *	
1		AHN, SEONG-DEOK, et al., "Surface Morphology Improvement of Metalorganic Chemical Vapor Deposition Al Films by Layered Deposition of Al and Ultrathin TiN", <u>Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers)</u> , 39(6A), (June 2000), 3349-3354	
		ALLEN, PETRA, "Atomic Layer deposition of Ta(Al)N(C) thin films using trimethylaluminum as a reducing agent", <u>Journal of the Electrochemical Society</u> , 148(10), (October 2001), G566-G571	
		CHENG, BAOHONG, et al., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100nm MOSFET's", <u>IEEE Transactions on Electron Devices</u> , 46(7), (July 1999), 1537-1544	
		CLARK-PHELPS, R. B., et al., "Engineered Tantalum Aluminate and Hafnium Aluminate ALD Films for Ultrathin Dielectric Films with Improved Electric and Thermal Properties", <u>Gate Stack and Silicide Issues in Silicon Processing II. Symposium (Materials Research Society Symposium Proceedings Vol.670)</u> , (Apr. 17, 2001), K2.2.1-6	
One		DESU, S B., "Minimization of Fatigue in Ferroelectric Films", <u>Physica Status Solidi A</u> , 151(2), (1995), 467-480 *	

* No month cited

EXAMINER

P. Wilson

DATE CONSIDERED

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 3815
	Examiner Name	Unknown A. Wilson
Sheet 4 of 7	Attorney Docket No: 1303.050US2	

ONE	ELAM, J W., "Kinetics of the WF6 and Si2H6 surface reactions during tungsten atomic layer deposition", <u>Surface Science</u> , 479(1-3), (May 2001),121-135	
	ENGELHARDT, M., "Modern Applications of Plasma Etching and Patterning in Silicon Process Technology", <u>Contributions to Plasma Physics</u> , 39(5), (1999),473-478 *	
	FUYUKI, TAKASHI, et al., "Electronic Properties of the Interface between Si and TiO2 Deposited at Very Low Temperatures", <u>Japanese Journal of Applied Physics</u> , Vol. 25, No. 9, (1986),1288-1291 *	
	GARTNER, M., et al., "Spectroellipsometric characterization of lanthanide-doped TiO/sub 2/ films obtained via the sol-gel technique", <u>Thin Solid Films</u> , 234(1-2), (1993),561-565 *	
	GELLER, S., et al., "Crystallographic Studies of Perovskite-like Compounds. II. Rare Earth Aluminates", <u>Acta Cryst.</u> Vol. 9, (May 1956),1019-1025	
	GIESS, E. A., et al., "Lanthanide gallate perovskite-type substrates for epitaxial, high-T/sub c/ superconducting Ba/sub 2/YCu/sub 3/O/sub 7- delta / films", <u>IBM Journal of Research and Development</u> , 34(6), (November 1990),916-926	
	GUSEV, E P., et al., "Ultrathin High-K Dielectrics Grown by Atomic Layer Deposition: A Comparative Study of ZrO2, HfO2, Y2O3 and Al2O3", <u>Electrochemical Society Proceedings Volume 2001-9</u> , (2001),189-195 *	
	HIRAYAMA, MASAKI, et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High Density Krypton Plasma", <u>International Electron Devices Meeting 1999. Technical Digest</u> , (1999),249-252 *	
	HUBBARD, K. J., et al., "Thermodynamic stability of binary oxides in contact with silicon", <u>Journal of Materials Research</u> , 11(11), (November 1996),2757-2776	
	HUNT, C. E., et al., "Direct bonding of micromachined silicon wafers for laser diode heat exchanger applications", <u>Journal of Micromechanics and Microengineering</u> , 1(3), (September 1991),152-156	
	JEONG, CHANG-WOOK, et al., "Plasma-Assisted Atomic Layer Growth of High-Quality Aluminum Oxide Thin Films", <u>Japanese Journal of Applied Physics, Part 1: Regular Papers and Short Notes and Review Papers</u> , 40(1), (January 2001),285-289	
	KEOMANY, D, et al., "Sol gel preparation of mixed cerium-titanium oxide thin films", <u>Solar Energy Materials and Solar Cells</u> , 33(4), (August 1994),429-441	
	KIM, C T., et al., "Application of Al2O3 Grown by Atomic Layer Deposition to DRAM and FeRAM", <u>International Symposium in Integrated Ferroelectrics</u> , (March 2000),316	
	KIM, D., et al., "Atomic Control of Substrate Termination and Heteroepitaxial Growth of SrTiO3/LaAlO3 Films", <u>Journal of the Korean Physical Society</u> , 36(6), (June 2000),444-448	
ONE	KIM, Y, et al., "Substrate dependence on the optical properties of Al/sub 2/O/sub 3/ films grown by atomic layer deposition", <u>Applied Physics Letters</u> , 71(25, 22), (December 1997),3604-3606	

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2815
	Examiner Name	Unknown A. WILSON
Sheet 5 of 7		Attorney Docket No: 1303.050US2

ONE	KRAUTER, G. , et al., "Room Temperature Silicon Wafer Bonding with Ultra-Thin Polymer Films", <u>Advanced Materials</u> , 9(5), (1997),417-420 *	
	KUKLI, KAUPÖ , "Atomic Layer Deposition of Titanium Oxide from TiI4 and H2O2", <u>Chemical Vapor Deposition</u> , 6(6), (2000),303-310 *	
	KUKLI, K , et al., "Controlled growth of yttrium oxysulphide thin films by atomic layer deposition", <u>Materials Science Forum</u> , 315-317, (1999),216-221 *	
	LEE, A E., et al., "Epitaxially grown sputtered LaAlO3 films", <u>Applied Physics Letters</u> , 57(19), (November 1990),2019-2021	
	LEE, CHENG-CHUNG , et al., "Ion-assisted deposition of silver thin films", <u>Thin Solid Films</u> , 359,(2000),pp. 95-97 *	
	LEE, JUNG-HYOUNG , et al., "Mass production worthy HfO/sub 2/-Al/sub 2/O/sub 3/ laminate capacitor technology using Hf liquid precursor for sub-100 nm DRAMs", <u>Electron Devices Meeting, 2002. IEDM '02. Digest. International</u> , (2002),221-224 *	
	LEE, DONG H., et al., "Metalorganic chemical vapor deposition of TiO/sub 2/-N anatase thin film on Si substrate", <u>Applied Physics Letters</u> , 66(7), (February 1995),815-816	
	LEE, L P., et al., "Monolithic 77 K dc SQUID magnetometer", <u>Applied Physics Letters</u> , 59(23), (December 1991),3051-3053	
	LESKELA, M. , et al., "ALD precursor chemistry: Evolution and future challenges", <u>J. Phys. IV France</u> , 9, (1999),837-852 *	
	LIU, C. T., "Circuit Requirement and Integration Challenges of Thin Gate Dielectrics for Ultra Small MOSFETs", <u>International Electron Devices Meeting 1998. Technical Digest</u> , (1998),747-750 *	
	LUCOVSKY, G , et al., "Microscopic model for enhanced dielectric constants in low concentration SiO/sub 2/-rich noncrystalline Zr and Hf silicate alloys", <u>Applied Physics Letters</u> , 77(18), (October 2000),2912-2914	
	MOLODYK, A A., et al., "Volatile Surfactant-Assisted MOCVD: Application to LaAlO3 Thin Film Growth", <u>Chemical Vapor Deposition</u> , 6(3), (June 2000),133-138	
	MOLSA, HEINI , et al., "Growth of yttrium oxide thin films from beta -diketonate precursor", <u>Advanced Materials for Optics and Electronics</u> , 4(6), (November-December 1994),389-400	
	MULLER, D. A., et al., "The electronic structure at the atomic scale of ultrathin gate oxides", <u>Nature</u> , 399(6738), (June 24, 1999),758-61	
	MULLER, D. A., et al., "The electronic structure at the atomic scale of ultrathin oxides", <u>Nature</u> , Vol. 399, <u>Nature</u> , Vol. 399,(1999),p. 752 *	
	NAKAJIMA, ANRI , et al., "NH/sub 3/-annealed atomic-layer-deposited silicon nitride as a high-k gate dielectric with high reliability", <u>Applied Physics Letters</u> , 80(7), (February 2002),1252-1254	
ONE	NEUMAYER, D A., et al., "Materials characterization of ZrO/sub 2/-SiO/sub 2/ and HfO/sub 2/-SiO/sub 2/ binary oxides deposited by chemical solution deposition", <u>Journal of Applied Physics</u> , 90(4), (August 15, 2001),1801-1808	

* No month cited.

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Sheet 6 of 7

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ave	NIEMINEN, MINNA , et al., "Formation and stability of lanthanum oxide thin films deposited from B-diketonate precursor", <u>Applied Surface Science</u> , 174(2), (April 16, 2001),155-165	
	OH, C B., et al., "Manufacturable embedded CMOS 6T-SRAM technology with high-k gate dielectric device for system-on-chip applications", <u>Technical Digest of International Electron Devices Meeting 2002</u> , (2002),423-426 *	
	OHRING, MILTON , "The Materials Science of Thin Films", <u>Boston : Academic Press</u> , (1992),118,121,125 *	
	OSTEN, H. J., et al., "High-k gate dielectrics with ultra-low leakage current based on praseodymium oxide", <u>International Electron Devices Meeting 2000. Technical Digest. IEDM</u> , (2000),653-656 *	
	PARK, BYUNG-EUN , et al., "Electrical properties of LaAlO3/Si and Sr0.8Bi2.2Ta2O9/LaAlO3/Si structures", <u>Applied Physics Letters</u> , 79(6), (August 2001),806-808	
	QI, WEN-JIE , et al., "MOSCAP and MOSFET characteristics using ZrO2 gate dielectric deposited directly on Si", <u>Electron Devices Meeting, 1999. IEDM Technical Digest. International</u> , (1999),145-148 *	
	RAYNER JR., G , et al., "The structure of plasma-deposited and annealed pseudo-binary ZrO2-SiO2 alloys", <u>Materials Research Society Symposium - Proceedings</u> , 611, (2000),C131-C139 *	
	RITALA, MIKKO , "Atomic Layer Epitaxy Growth of Titanium, Zirconium and Hafnium Dioxide Thin Films", <u>Annales Academiae Scientiarum Fennicae</u> , (1994),24-25 *	
	ROTONDARO, A L., et al., "Advanced CMOS Transistors with a Novel HfSiON Gate Dielectric", <u>Symposium on VLSI Technology Digest of Technical Papers</u> , (2002),148-149 *	
	SAITO, YUJI , et al., "Advantage of Radical Oxidation for Improving Reliability of Ultra-Thin Gate Oxide", <u>2000 Symposium on VLSI Technology Digest of Technical Papers</u> , (2000),176-177 *	
	SAITO, YUJI , et al., "High-Integrity Silicon Oxide Grown at Low-Temperature by Atomic Oxygen Generated in High-Density Krypton Plasma", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),152-153 *	
	SHANWARE, A , et al., "Reliability evaluation of HfSiON gate dielectric film with 12.8 A SiO2 equivalent thickness", <u>International Electron Devices Meeting. Technical Digest</u> , (2001),137-140 *	
	SHIN, CHANG H., et al., "Fabrication and Characterization of MFISFET using Al2O3 Insulating Layer for Non-Volatile Memory", <u>12th International Symposium in Integrated Ferroelectrics</u> , (March 2000),1-9	
	SNEH, OFER , et al., "Thin film atomic layer deposition equipment for semiconductor processing", <u>Thin Solid Films</u> , 402(1-2), (Jan. 1, 2002),248-261	
one	SONG, HYUN-JUNG , et al., "Atomic Layer Deposition of Ta2O5 Films Using Ta(OC2H5)5 and NH3", <u>Ultrathin SiO/sub 2/ and High-K Materials for ULSI Gate Dielectrics. Symposium</u> , (1999),469-471 *	

* No mention cited.

EXAMINER

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OK	SUNTOLA, T. , "Atomic Layer Epitaxy", <u>Handbook of Crystal Growth, 3: Thin Films of Epitaxy, Part B: Growth Mechanics and Dynamics</u> , Amsterdam, (1994), 602-663 *	
	SUNTOLA, T. , "Atomic layer epitaxy", <u>Thin Solid Films</u> , 216(1), (August 28, 1992), 84-89	
	VAN DOVER, R B., "Amorphous lanthanide-doped TiOx dielectric films", <u>Applied Physics Letters</u> , 74(20), (May 1999), 3041-3043	
	VIIROLA, H. , "Controlled growth of antimony-doped tin dioxide thin films by atomic layer epitaxy", <u>Thin Solid Films</u> , 251, (November 1994), 127-135	
	VIIROLA, H. , "Controlled growth of tin oxide thin films by atomic layer epitaxy", <u>Thin Solid Films</u> , 249(2), (September 1994), 144-149	
	VISOKAY, M R., "Application of HfSiON as a gate dielectric material", <u>Applied Physics Letters</u> , 80(17), (April 2002), 3183-3185	
	WILK, G D., et al., "Hafnium and zirconium silicates for advanced gate dielectrics", <u>Journal of Applied Physics</u> , 87(1), (January 2000), 484-492	
	WILK, G. D., et al., "High-K gate dielectrics: Current status and materials properties considerations", <u>Journal of Applied Physics</u> , 89(10), (May 2001), 5243-5275	
OK	ZUCKER, O , et al., "Application of Oxygen Plasma Processing to Silicon Direct Bonding", <u>Sensors and Actuators A</u> , 36, (1993), 227-231 *	

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----------	---	-----------------	---------

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Group Art Unit	2812 2815
Examiner Name	Unknown A. Wilson

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Attorney Docket No: 1303.050US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
AW	US-2002/00001971-A1	01/03/2002	Cho, Hag-ju	06/27/2001
	US-2002/0111001	08/15/2002	Ahn, Kie Y., et al.	02/09/2001
	US-2002/0122885	09/05/2002	Ahn, Kie Y.	03/01/2001
	US-2002/0195056	12/26/2002	Sandhu, G., et al.	12/26/2002
	US-2003/0003722	01/02/2003	Vaartstra, Brian A.	08/19/2002
	US-2003/0157764	08/21/2003	Ahn, Kie Y., et al.	02/20/2002
	US-2003/0209324-A1	11/13/2003	Fink, S. T.	03/31/2003
	US-2003/0227033	12/11/2003	Ahn, Kie Y., et al.	06/05/2002
	US-2003/0228747	12/11/2003	Ahn, Kie Y., et al.	06/05/2002
	US-2004/0004245	01/08/2004	Forbes, Leonard, et al.	07/08/2002
	US-2004/0004247	01/08/2004	Forbes, Leonard, et al.	07/08/2002
	US-2004/0033681	02/19/2004	Ahn, Kie Y., et al.	08/15/2002
	US-2004/0033701-A1	02/19/2004	Ahn, K. Y., et al.	08/15/2002
	US-2004/0038525-A1	02/26/2004	Meng, S., et al.	08/26/2002
	US-4,058,430	11/15/1977	Suntola, T., et al.	11/25/1975
	US-4,725,877	02/16/1988	Brasen, Daniel, et al.	04/11/1986
	US-6,010,969	01/04/2000	Vaarstra, Brian A.	10/02/1996
	US-6,203,726	03/20/2001	Danielson, Earl, et al.	10/07/1999
	US-6,225,237	05/01/2001	Vaartstra, Brian A.	09/01/1998
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	02/27/1998
	US-6,273,951	08/14/2001	Vaartstra, Brian A.	06/16/1999
	US-6,368,398	04/09/2002	Vaartstra, Brian A.	01/19/2001
	US-6,451,641	09/17/2002	Halliyl, Arvind, et al.	02/27/2002
	US-6,495,436	12/17/2002	Ahn, Kie Y., et al.	02/09/2001
	US-6,527,866	03/04/2003	Matijasevic, Vladimir, et al.	02/09/2000
	US-6,531,354	03/11/2003	Maria, J., et al.	01/17/2001
	US-6,537,613	03/25/2003	Senzaki, Y., et al.	04/10/2000
	US-6,586,349	07/01/2003	Jeon, J. S., et al.	02/21/2002
	US-6,645,882	11/11/2003	Halliyl, Arvind, et al.	01/17/2002
	US-6,660,660	12/09/2003	Haukka, S. P., et al.	08/31/2001
	US-6,713,846	03/30/2004	Senzaki, Y.	01/25/2002
AW	US-6,730,575	05/04/2004	Eldridge, Jerome M.	08/30/2001
	US-6,750,066	06/15/2004	Cheung, F. T., et al.	04/08/2002

CLASS 360

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T*
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Substitute Disclosure Statement Form (PTO-1449)

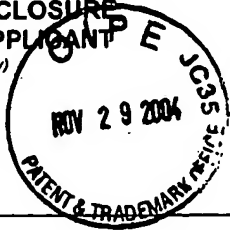
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Complete if Known

Application Number	10/789,042
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First Named Inventor	Ahn, Kie
Group Art Unit	2812 2815
Examiner Name	Unknown A. WILSON

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<i>bae</i>		TAKEMOTO, J. H., et al., "Microstrip Resonators and Filters Using High-TC Superconducting Thin Films on LaAlO ₃ ", <u>IEEE Transaction on Magnetics</u> , 27(2), (March 1991), 2549-2552	

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